

# High Voltage Power MOSFET w/ Extended FBSOA

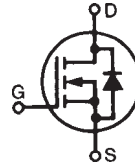
## IXTN5N250

$$V_{DSS} = 2500V$$

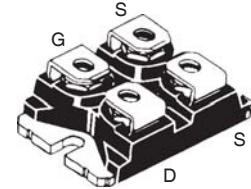
$$I_{D25} = 5A$$

$$R_{DS(on)} \leq 8.8\Omega$$

N-Channel Enhancement Mode  
Avalanche Rated  
Guaranteed FBSOA



miniBLOC  
E153432



G = Gate      D = Drain  
S = Source

Either Source Terminal S can be used as the Source Terminal or the Kelvin Source (Gate Return) Terminal.

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $150^\circ C$	2500	V
$V_{DGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$	2500	V
$V_{GSS}$	Continuous	$\pm 30$	V
$V_{GSM}$	Transient	$\pm 40$	V
$I_{D25}$	$T_C = 25^\circ C$	5	A
$I_{DM}$	$T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$	20	A
$I_A$	$T_C = 25^\circ C$	2.5	A
$E_{AS}$	$T_C = 25^\circ C$	2.5	J
$P_D$	$T_C = 25^\circ C$	700	W
$T_J$		-55 to +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 to +150	$^\circ C$
$V_{ISOL}$	50/60 Hz, RMS, $t = 1$ minute	2500	V~
	$I_{ISOL} \leq 1mA$ , $t = 1s$	3000	V~
$M_d$	Mounting Torque for Base Plate	1.5/13	Nm/lb.in.
	Terminal Connection Torque	1.3/11.5	Nm/lb.in.
<b>Weight</b>		30	g

### Features

- International Standard Package
- Molding Epoxies Meet UL94 V-0 Flammability Classification
- Guaranteed FBSOA at  $75^\circ C$
- miniBLOC with Aluminum Nitride Isolation
- Low Package Inductance

### Advantages

- Easy to Mount
- Space Savings
- High Power Density

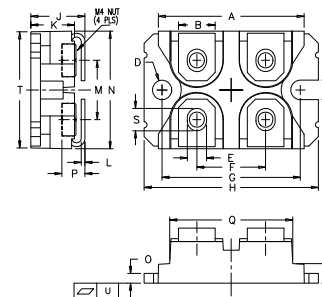
### Applications

- High Voltage Power Supplies
- Capacitor Discharge
- Pulse Circuits

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 1mA$	2500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 1mA$	2.0		5.0 V
$I_{GSS}$	$V_{GS} = \pm 30V$ , $V_{DS} = 0V$			$\pm 200$ nA
$I_{DSS}$	$V_{DS} = 2kV$ , $V_{GS} = 0V$ $T_J = 125^\circ C$			50 $\mu A$ 4 mA
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1			8.8 $\Omega$

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values			
		Min.	Typ.	Max.	
$g_{fs}$	$V_{DS} = 50\text{V}$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1	3.0	4.5	6.0	S
$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$		8560		pF
$C_{oss}$			315		pF
$C_{rss}$			90		pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$ $R_G = 1\Omega$ (External)		33		ns
$t_r$			20		ns
$t_{d(off)}$			90		ns
$t_f$			44		ns
$Q_{g(on)}$		$V_{GS} = 10\text{V}$ , $V_{DS} = 1000\text{V}$ , $I_D = 0.5 \cdot I_{D25}$		200	
$Q_{gs}$			28		nC
$Q_{gd}$			70		nC
$R_{thJC}$				0.18	$^\circ\text{C/W}$
$R_{thCS}$		0.05			$^\circ\text{C/W}$

### SOT-227B (IXTN) Outline



(M4 screws (4x) supplied)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

### Safe Operating Area Specification

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
SOA	$V_{DS} = 2000\text{V}$ , $I_D = 0.11\text{A}$ , $T_C = 75^\circ\text{C}$ , $tp = 3\text{s}$	220		W

### Source-Drain Diode

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values			
		Min.	Typ.	Max.	
$I_S$	$V_{GS} = 0\text{V}$			5	A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			20	A
$V_{SD}$	$I_F = I_S$ , $V_{GS} = 0\text{V}$ , Note 1			1.5	V
$t_{rr}$	$I_F = 2.5\text{A}$ , $-di/dt = 100\text{A}/\mu\text{s}$ , $V_R = 100\text{V}$		1.2		$\mu\text{s}$

Note: 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

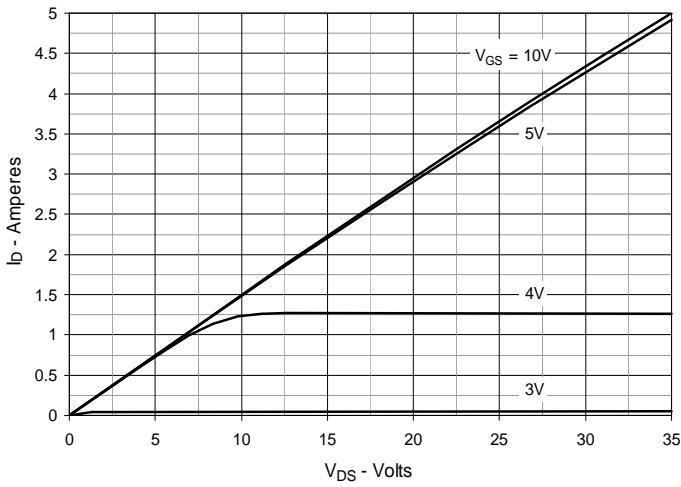
### PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

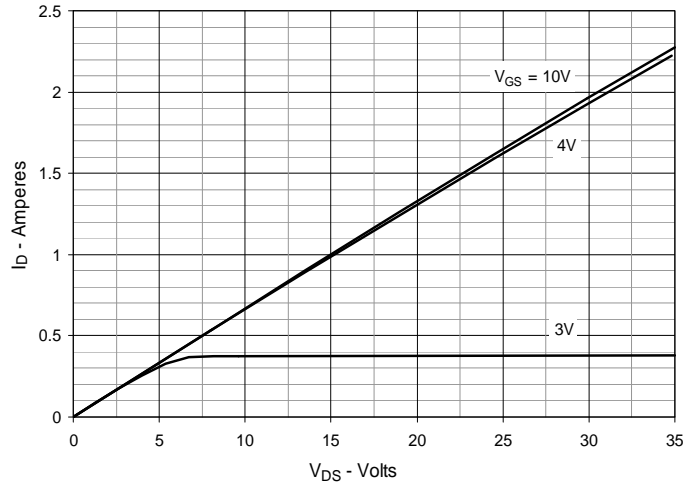
IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

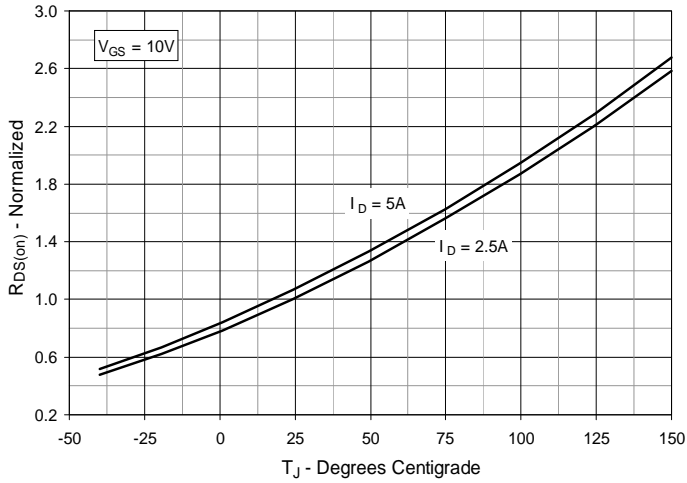
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



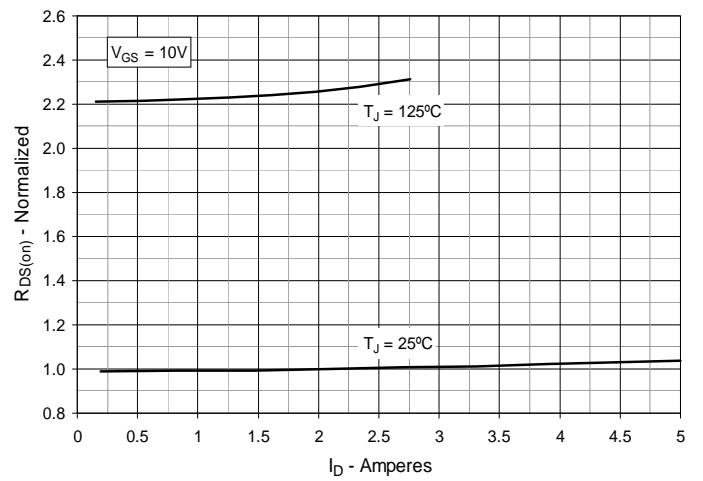
**Fig. 2. Output Characteristics @  $T_J = 125^\circ\text{C}$**



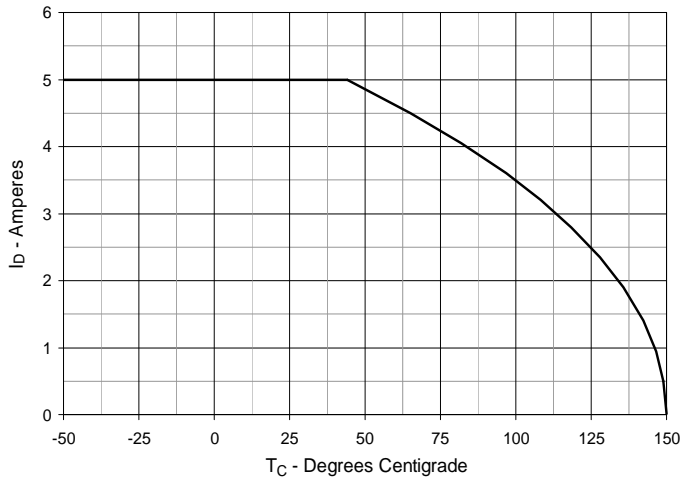
**Fig. 3.  $R_{DS(on)}$  Normalized to  $I_D = 2.5\text{A}$  Value vs. Junction Temperature**



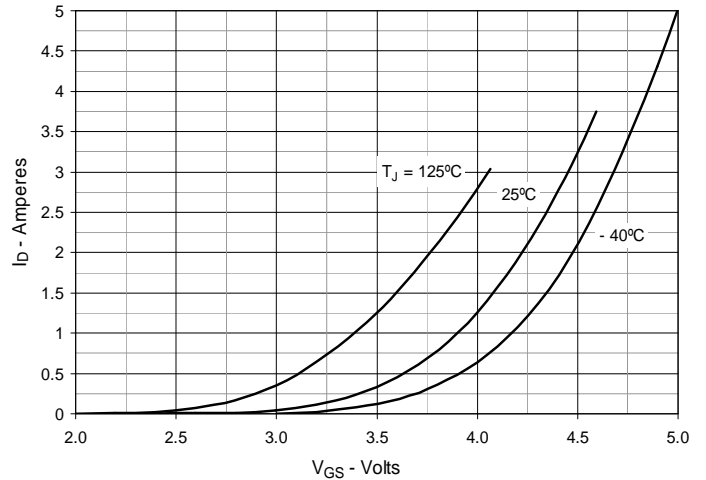
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 2.5\text{A}$  Value vs. Drain Current**



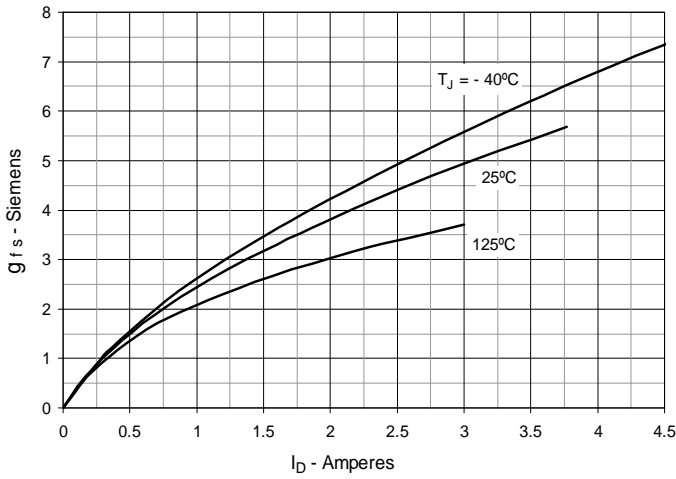
**Fig. 5. Maximum Drain Current vs. Case Temperature**



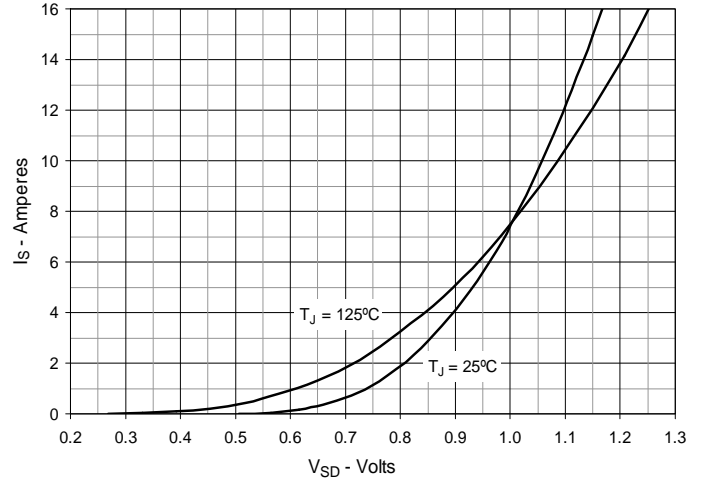
**Fig. 6. Input Admittance**



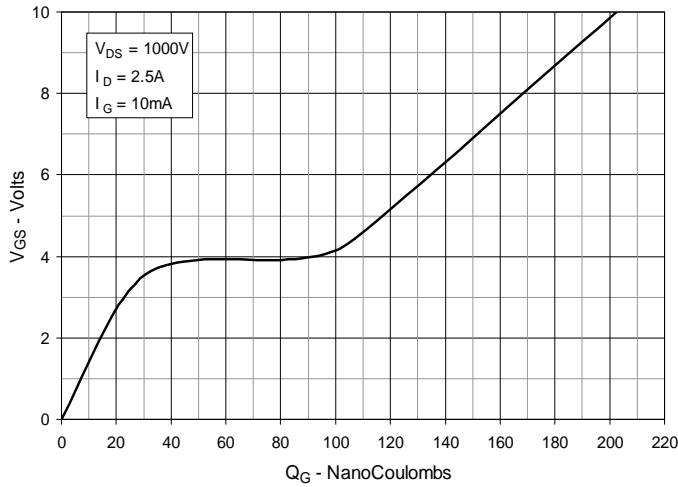
**Fig. 7. Transconductance**



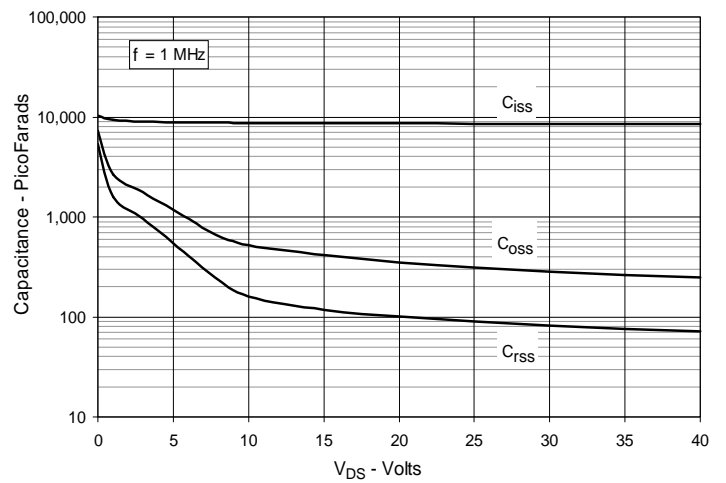
**Fig. 8. Forward Voltage Drop of Intrinsic Diode**



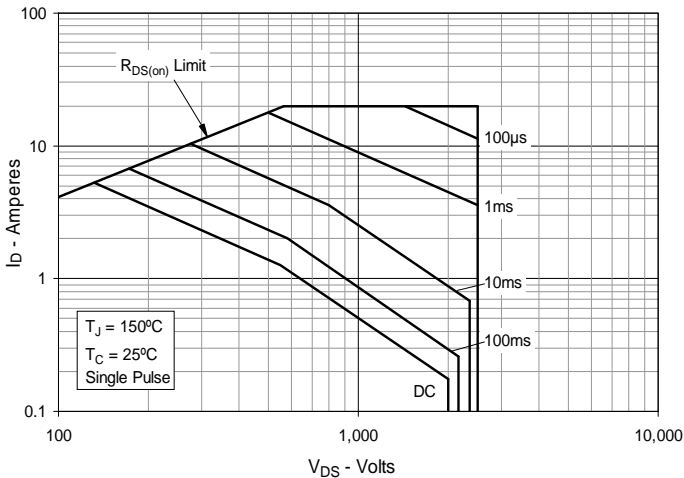
**Fig. 9. Gate Charge**



**Fig. 10. Capacitance**



**Fig. 11. Forward-Bias Safe Operating Area @  $T_C = 25^\circ\text{C}$**



**Fig. 12. Forward-Bias Safe Operating Area @  $T_C = 75^\circ\text{C}$**

